

#### FEATURES

- High Power  $P_{1dB}=33dBm(TYP.)$
- High Gain  $G_{1dB}=25dB(TYP.)$
- High Power Added Efficiency  $\eta_{add}=14\%(TYP.)$
- Operable Frequency :  $f=10.0-12.0GHz.$

#### ABSOLUTE MAXIMUM RATINGS( $T_a=25^{\circ}C$ )

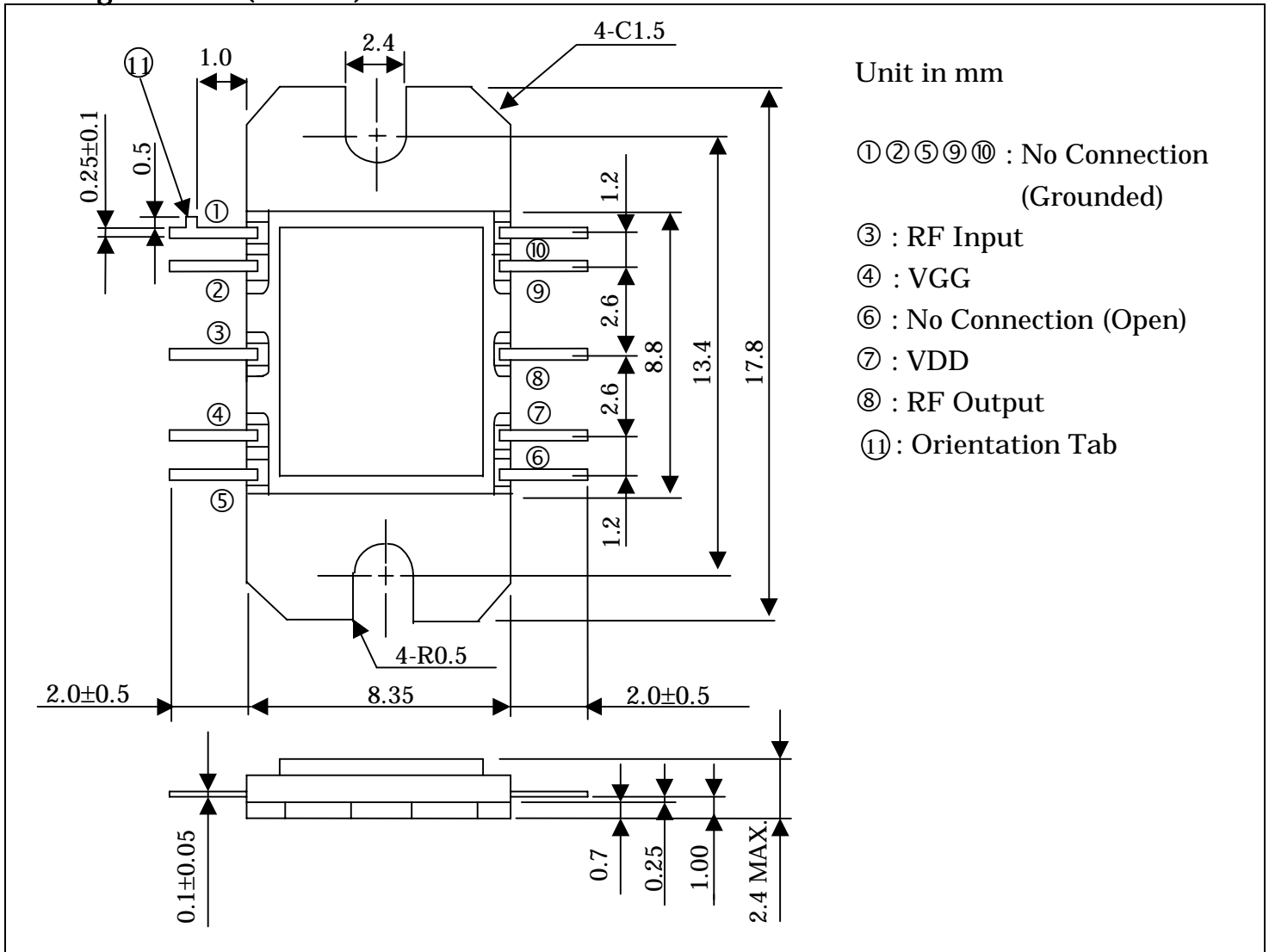
CHARACTERISTICS	SYMBOL	UNIT	RATINGS
DRAIN SUPPLY VOLTAGE	VDD	V	15
GATE SUPPLY VOLTAGE	VGG	V	-10
INPUT POWER	Pin	dB	7
FLANGE TEMPERATURE	Tf	°C	-30 to +80
STORAGE TEMPERATURE	Tstg	°C	-65 to +175

#### RF PERFORMANCE SPECIFICATIONS ( $T_a=25^{\circ}C$ )

CHARACTERISTICS	SYMBOL	CONDITION	UNIT	MIN.	TYP.	MAX.
Operating Frequency	f		GHz	10.0	—	12.0
Output Power at 1dB Gain Compression Point	P1dB	VDD=10V VGG= -5V	dBm	31	33	—
Power Gain at 1dB Gain Compression Point	G1dB		dB	21	25	—
Gain Flatness	$\Delta G$		dB	—	—	2.5
Drain Current	IDD		A	—	1.4	1.8
Power Added Efficiency	$\eta_{add}$	2 Tone @ Po=19dBm(SCL)	%	—	14	—
Third Order Intermodulation Distortion	IM3		dBc	-42	-45	—
VSWRin (small signal)	VSWRin		—	—	2.0	3.0

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## Package Outline (2-9E1D)



## Recommended Bias Configuration

